

Poster session is held based on the even/odd numbers of the posters.

Poster session A, Odd numbers: March 8th, (Mon) 13:00-14:30

Poster session A, Even numbers: March 8th, (Mon) 17:30-19:00

- PA001A **Film Depositions Using Pulsed Magnetron Systems of Several Types**  
J. Vlcek  
University of West Bohemia, Czech Republic
- PA002A **Investigation on Plasma Parameters in Inductively Coupled Ar/H<sub>2</sub> Plasmas**  
H. Kasugai and T. Kimura  
Nagoya Institute of Technology, Japan
- PA003A **Periodic Peak Formation in O<sup>-</sup> Energy Distribution in RF Magnetron Plasma**  
<sup>1</sup>K. Goto, <sup>1</sup>T. Ishijima, <sup>2</sup>T. Morita, <sup>3</sup>N. Ohshima, <sup>3</sup>K. Kinoshita and <sup>1</sup>H. Toyoda  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>ULVAC, Inc., Japan  
<sup>3</sup>NEC Corporation, Japan
- PA004A **Volumetric Role of Acetic Acid in the Hydrolysis of TTIP Solution**  
S. Parajulee, M. Hayakawa and S. Ikezawa  
Chubu University, Japan
- PA005A **Diagnostics of Inertial Plasma Parameters in a Plasma Array Using Metamaterial Effects**  
<sup>1</sup>O. Sakai, <sup>1</sup>T. Naito, <sup>1</sup>T. Shimomura, <sup>1</sup>D-S. Lee and <sup>2</sup>K. Tachibana  
<sup>1</sup>Kyoto University, Japan  
<sup>2</sup>Ehime University, Japan
- PA006A **Electrical Extraction of One Dimensional MOSFET Doping Profiles by Threshold Voltage Measurement**  
<sup>1,2</sup>H. H. Park and <sup>2</sup>B.D. Choi  
<sup>1</sup>Samsung Electronics Co., Korea  
<sup>2</sup>Sungkyunkwan University, Korea

- PA007A **Accurate Monitoring System for Silicon Wafer Temperature Using Super-Continuum Light Source on Low-Coherence Interferometry**  
<sup>1</sup>T. Hiraoka, <sup>1</sup>T. Kageyama, <sup>1,2</sup>C. Koshimizu, <sup>1</sup>T. Ohta, <sup>3</sup>M. Ito, <sup>4</sup>N. Nishizawa and <sup>5</sup>M. Hori  
<sup>1</sup>Wakayama University, Japan  
<sup>2</sup>Tokyo Electron AT Ltd., Japan  
<sup>3</sup>Meijo University, Japan  
<sup>4</sup>Osaka University, Japan  
<sup>5</sup>Nagoya University, Japan
- PA008A **Investigation of Formation Mechanism of Indium-Zinc-Oxide Film by RF Magnetron Sputtering**  
<sup>1</sup>T. Kanae, <sup>1</sup>M. Inoue, <sup>1</sup>N. Takota, <sup>1</sup>T. Ohta, <sup>2</sup>M. Ito, <sup>3</sup>Y. Higashijima, <sup>4</sup>H. Kano, <sup>5</sup>S. Den and <sup>6</sup>M. Hori  
<sup>1</sup>Wakayama University, Japan  
<sup>2</sup>Meijo University, Japan  
<sup>3</sup>NU System Co., Ltd., Japan  
<sup>4</sup>NU Eco Engineering Co., Ltd., Japan  
<sup>5</sup>Katagiri Engineering Co., Ltd., Japan  
<sup>6</sup>Nagoya University, Japan
- PA009A **Plasma Diagnostics of a Magnetron Sputtering Device with an Extraordinary Strong Magnetic Field**  
K. Nakamura, M. Aoyama and H. Ikuta  
Nagoya University, Japan
- PA010A **Influence of High-Energy Secondary Electrons in Plasma Immersion Ion Implantation**  
<sup>1,2</sup>Y. Guo, <sup>1</sup>K. Nakamura, <sup>2</sup>J. Shi, <sup>2</sup>J. Zhang, <sup>1</sup>Y. Nakano and <sup>1</sup>H. Sugai  
<sup>1</sup>Chubu University, Japan  
<sup>2</sup>Donghua University, China
- PA011A **Spectroscopic Study of Plasma in Aqueous Solution: (1) Time-Resolved Emission Spectroscopy of Active Species**  
Y. Someya, H. Kato, Y. Kusama and H. Yui  
Tokyo University of Science, Japan
- PA012A **Spectroscopic Study of Plasma in Aqueous Solution: (2) Optical Emission Spectroscopy with High Spatial Resolution**  
Y. Kusama, H. Kato, Y. Someya and H. Yui  
Tokyo University of Science, Japan
- PA013A **Mixing-Process of Fine-Particles into the Plasma Produced in Microwave Heating of Powder Material**  
<sup>1</sup>A. Matsubara, <sup>1</sup>K. Nakayama, <sup>1</sup>S. Okajima and <sup>2</sup>M. Sato  
<sup>1</sup>Chubu University, Japan  
<sup>2</sup>National Institute of Fusion Science, Japan

- PA014A **Plasma Diagnostics for NH<sub>3</sub> Plasmas Using a Quartz Sensor at Various Pressures**  
A. Suzuki and H. Nonaka  
National Institute of Advanced Industrial Science and Technology (AIST), Japan
- PA015A **Surface Loss Probabilities of H Atom on Various Silicon Thin Films**  
<sup>1</sup>Y. Abe, <sup>1</sup>C. S. Moon, <sup>1</sup>S. Kawashima, <sup>1</sup>K. Takeda, <sup>1</sup>H. Kondo, <sup>2</sup>K. Ishikawa, <sup>2,3</sup>M. Sekine and <sup>1,2,3</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Plasma Nanotechnology Research Center, Japan  
<sup>3</sup>JST, CREST, Japan
- PA016A **Measurement of H Radical Density in H<sub>2</sub>/Ar Nonequilibrium Atmospheric Pressure Plasma**  
<sup>1</sup>H. Inui, <sup>1</sup>Y. Matsudaira, <sup>2</sup>N. Yoshida, <sup>2</sup>N. Iwaki, <sup>2</sup>T. Kawasumi, <sup>1</sup>K. Takeda, <sup>1</sup>K. Ishikawa, <sup>1</sup>H. Kondo, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Fuji Machine Mfg. Co., Ltd, Japan
- PA017A **Modification of the Simulation Code ACAT to Treat Real Atomic Positions**  
<sup>1</sup>A. Takayama, <sup>1</sup>A. Ito, <sup>1,2</sup>H. Nakamura, <sup>2</sup>S. Saito and <sup>3</sup>T. Kenmotsu  
<sup>1</sup>National Institute for Fusion Science, Japan  
<sup>2</sup>Nagoya University, Japan  
<sup>3</sup>Doshisha University, Japan
- PA018A **Simulation of High-Pressure Helium DC Glow Discharge Plasmas**  
K. Yamada, A. Oda and T. Kimura  
Nagoya Institute of Technology, Japan
- PA019A **Molecular Dynamics Simulation of Hydrogen Injection onto Diamond and Diamond Like Carbon Surfaces**  
<sup>1,2</sup>H. Nakamura, <sup>1</sup>A. Ito, <sup>1</sup>A. Takayama, <sup>2</sup>S. Saito, <sup>2</sup>N. Ohno and <sup>2</sup>S. Kajita  
<sup>1</sup>National Institute for Fusion Science, Japan  
<sup>2</sup>Nagoya University, Japan
- PA020A **Modeling of Radical Transformation under 'PAPE' Structure and Method of Estimation for Surface Loss Probabilities of Radicals**  
<sup>1,2,3</sup>A. Malinowski, <sup>1</sup>M. Hori, <sup>1</sup>M. Sekine, <sup>1</sup>T. Suzuki, <sup>1</sup>H. Yamamoto, <sup>1</sup>H. Kondo, <sup>1</sup>K. Ishikawa, <sup>2</sup>A. Jakubowski, <sup>2</sup>L. Lukasiak and <sup>3</sup>D. Tomaszewski  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Warsaw University of Technology, Poland  
<sup>3</sup>Institute of Electron Technology, Poland

- PA021A **Bias Annealing of Defects in Silicon pn Diodes Irradiated by Protons**  
<sup>1</sup>H. Sakane, <sup>1</sup>J. Ito, <sup>2</sup>Y. Nagae, <sup>2</sup>M. Nakai, <sup>2</sup>K. Furuhashi and <sup>2</sup>Y. Tokuda  
<sup>1</sup>S. H. I. Examination & Inspection, Ltd., Japan  
<sup>2</sup>Aichi Institute of Technology, Japan
- PA022A **Improvement of RIE Lag in High Aspect Ratio Si Etching**  
J. M. Ji, W-S. Shin and C-K. Kim  
Ajou University, Korea
- PA023A **Behavior of Rotational Temperature in Dual Frequency Capacitively Coupled Plasma**  
<sup>1</sup>T. Yamaguchi, <sup>1</sup>T. Kimura, <sup>1</sup>K. Takeda, <sup>2</sup>C. Koshimizu, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Tokyo Electron AT Ltd., Japan
- PA024A **Control and Diagnostics of Oxygen Microwave Plasma at High Pressure**  
<sup>1</sup>S. Ohta, <sup>1</sup>S. Fujita, <sup>1</sup>I. Liang, <sup>2</sup>K. Kato, <sup>1</sup>K. Nakamura and <sup>1</sup>H. Sugai  
<sup>1</sup>Chubu University, Japan  
<sup>2</sup>Nagoya Industrial Research Institute, Japan
- PA025A **Investigation into Body-Bias Dependence of Drain-Induced Barrier Lowering for Sphere-Shaped-Recess-Cell-Array Transistor**  
<sup>1,2</sup>K. Kim, <sup>1</sup>K-H. Jung, <sup>1</sup>J-S. Moon and <sup>2</sup>Y. Roh  
<sup>1</sup>Samsung Electronics, Korea  
<sup>2</sup>Sungkyunkwan University, Korea
- PA026A **Study for Damage in Porous SiOCH Film with Air Exposure After H<sub>2</sub> or N<sub>2</sub> Plasma Treatment**  
<sup>1</sup>T. Suzuki, <sup>1</sup>H. Yamamoto, <sup>1,2</sup>K. Takeda, <sup>1,2</sup>M. Sekine and <sup>1,2</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>JST, CREST, Japan
- PA027A **Porous SiOCH Low-*k* Film Etch Process and its Surface Reactions Employing an Alternative Fluorocarbon Gas C<sub>3</sub>F<sub>10</sub>O**  
<sup>1</sup>E. Shibata, <sup>1</sup>M. Sekine, <sup>1</sup>K. Ishikawa, <sup>1</sup>H. Kondo, <sup>2</sup>H. Okamoto and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Asahi Glass Co., Ltd., Japan
- PA028A **SiO<sub>2</sub> Contact Hole Etch Mechanism Using Environment-Friendly New Gas, C<sub>5</sub>F<sub>7</sub>H**  
<sup>1</sup>Y. Miyawaki, <sup>1</sup>K. Takeda, <sup>2</sup>A. Ito, <sup>2</sup>M. Nakamura, <sup>1</sup>H. Kondo, <sup>1</sup>K. Ishikawa, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Zeon Corporation, Japan

- PA029A **Effect of CF Layer on Porous SiOCH Low- $k$  Films During H<sub>2</sub> or N<sub>2</sub> Plasma Exposure**  
H. Yamamoto, K. Takeda, M. Sekine and M. Hori  
Nagoya University, Japan
- PA030A **Analysis of ArF Photoresist Modified by Fluorocarbon Ion Bombardment**  
<sup>1</sup>T. Takeuchi, <sup>1</sup>M. Sekine, <sup>1</sup>H. Toyoda, <sup>1</sup>H. Kondo, <sup>1</sup>K. Ishikawa, <sup>1</sup>K. Takeda, <sup>2</sup>S-Y. Kang, <sup>2</sup>I. Sawada and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Tokyo Electron Ltd., Japan
- PA031A **Deep-Level Defect Passivation by High Density Hydrogen Radical Exposures on Ion Irradiated Si**  
<sup>1</sup>S. Chen, <sup>2</sup>Y. Nagae, <sup>2</sup>M. Nakai, <sup>1</sup>K. Ishikawa, <sup>1</sup>H. Kondo, <sup>3</sup>H. Kano, <sup>1</sup>K. Takeda, <sup>2</sup>T. Tokuda, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Aichi Institute of Technology, Japan  
<sup>3</sup>NU Eco-Engineering Co., Ltd, Japan
- PA032A **Measurement of Si Wafer Temperature with Metal Thin Film during Plasma Process Using Low-Coherence Interferometer**  
<sup>1</sup>H. Kuroda, <sup>2</sup>H. Sugiura, <sup>1</sup>H. Yamamoto, <sup>2</sup>M. Ito, <sup>3</sup>T. Ohta, <sup>1</sup>K. Takeda, <sup>1</sup>H. Kondo, <sup>1</sup>K. Ishikawa, <sup>1,4</sup>M. Sekine and <sup>1,4</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Meijo University, Japan  
<sup>3</sup>Wakayama University, Japan  
<sup>4</sup>JST, CREST, Japan
- PA033C **A Study on Surface Plasma Treatment of Polyimide Film for Cu Metallization**  
T. Nguyen, S-J. Cho, J-W. Choi and J-H. Boo  
Sungkyunkwan University, Korea
- PA034B **High-Quality InAlN Lattice Matched to GaN Grown by Metal Organic Chemical Vapor Deposition**  
Z. T. Chen, Y. Sakai and T. Egawa  
Nagoya Institute of Technology, Japan
- PA035B **Photoelectrochemical Evaluation of Bulk GaN Single Crystal Dependent on Growth Method**  
K. Fujii, T. Kato, K. Sato, K. Koike, T. Yamada, H. Yamane and T. Yao  
Tohoku University, Japan
- PA036B **Low Pressure HVPE Growth of AlN on 6H-SiC**  
<sup>1</sup>K. Okumura, <sup>1</sup>H. Miyake, <sup>1</sup>K. Hiramatsu and <sup>2</sup>O. Eryuu  
<sup>1</sup>Mie University, Japan  
<sup>2</sup>Nagoya Institute of Technology, Japan

- PA037B **Infrared Reflectance Spectra of (1-101)GaN Grown on a (001)Si Substrate**  
<sup>1</sup>N. Sawaki, <sup>1</sup>K. Otsuka, <sup>1</sup>S. Iwata, <sup>1</sup>A. Ogawa, <sup>1</sup>K. Kondo, <sup>2</sup>Y. Honda, <sup>2</sup>T. Tanikawa, <sup>2</sup>T. Hikosaka and <sup>2</sup>M. Yamaguchi  
<sup>1</sup>Aichi Institute of Technology, Japan  
<sup>2</sup>Nagoya University, Japan
- PA038B **Growth of GaN Epilayer Using AlN Buffer on Patterned Sapphire Substrate by Metalorganic Chemical Vapor Deposition**  
<sup>1</sup>N. H. Kim, <sup>1</sup>K-H. Lee, <sup>1</sup>S. H. Park, <sup>1</sup>J. H. Kim, <sup>1</sup>M. H. Kim, <sup>2</sup>H-K. Yuh, <sup>2</sup>Y. Moon, <sup>2</sup>S. K. Shee and <sup>1</sup>E. Yoon  
<sup>1</sup>Seoul National University, Korea  
<sup>2</sup>THELEDS Co., Ltd., Korea
- PA039B **MOCVD Growth of GaN Layer Using InN Interlayer and its Influence on Residual Thermal Strain**  
<sup>1</sup>K-H. Lee, <sup>1</sup>S. H. Park, <sup>1</sup>J. H. Kim, <sup>1</sup>N. H. Kim, <sup>1</sup>M. H. Kim, <sup>2</sup>H. Na, <sup>1,3</sup>Y. Nanishi and <sup>1</sup>E. Yoon  
<sup>1</sup>Seoul National University, Korea  
<sup>2</sup>Daejin University, Korea  
<sup>3</sup>Ritsumeikan University, Japan
- PA040B **Reduction of Threading Dislocation Density in GaN Using an GaN:C Interlayer**  
<sup>1</sup>S. H. Park, <sup>1</sup>K-H. Lee, <sup>1</sup>N. H. Kim, <sup>1</sup>D. Moon, <sup>1,2</sup>Y. Nanishi and <sup>1</sup>E. Yoon  
<sup>1</sup>Seoul National University, Korea  
<sup>2</sup>Ritsumeikan University, Japan
- PA041B **Deep-Level Optical Spectroscopy Study of Band-Gap States in *n*-GaN Epilayers Using Transparent Polyaniline Schottky Contacts**  
<sup>1</sup>Y. Nakano, <sup>2</sup>N. Matsuki, <sup>2</sup>Y. Irokawa and <sup>2</sup>M. Sumiya  
<sup>1</sup>Chubu University, Japan  
<sup>2</sup>National Institute for Materials Science, Japan
- PA042B **Novel Power Conversion Circuit Using GaN Switching Device**  
<sup>1</sup>M. Saito, <sup>2</sup>M. Iwasaki, <sup>2</sup>T. Egawa and <sup>2</sup>N. Matsui  
<sup>1</sup>Shibaura Institute of Technology, Japan  
<sup>2</sup>Nagoya Institute of Technology, Japan
- PA043B **Dependence of Epi-Layer Thickness on the Vertical Breakdown of AlGaIn/GaN HEMTs Grown on Silicon**  
I. B. Rowena, S. L. Selvaraj, T. Suzue and T. Egawa  
Nagoya Institute of Technology, Japan

- PA044B **Effect of Drain Disturb According to the Nitrogen Concentration in the Tunnel Oxide of NOR Flash Memory**  
<sup>1,2</sup>W. Lee, <sup>1</sup>J. Jee, <sup>1</sup>J. Han, <sup>1</sup>Y. You, <sup>1</sup>S. Kim, <sup>1</sup>C-J. Kang, <sup>1</sup>J-T. Moon and <sup>2</sup>Y. Roh  
<sup>1</sup>Samsung Electronics, Korea  
<sup>2</sup>Sungkyunkwan University, Korea
- PA045B **High Temperature Operation of Normally Off AlGaIn /GaIn Heterostructure Field-Effect Transistors with p-GaN Gate**  
T. Sugiyama, D. Iida, M. Iwaya, S. Kamiyama, H. Amano and I. Akasaki  
Meijo University, Japan
- PA046B **AlN Growth on Trench-Patterned AlN/Sapphire by Low-Pressure HVPE**  
<sup>1</sup>K. Fujita, <sup>1</sup>K. Okuura, <sup>1</sup>H. Miyake, <sup>1</sup>K. Hiramatsu, <sup>2</sup>J. Norimatsu and <sup>2</sup>H. Hirayama  
<sup>1</sup>Mie University, Japan  
<sup>2</sup>Riken, Japan
- PA047B **Growth of High-Quality AlN on *a*-Plane Sapphire by HVPE**  
Y. Takagi, J. Wu, H. Miyake and K. Hiramatsu  
Mie University, Japan
- PA048B **Dislocation Decrease of Semi-Polar GaN on Si Substrate by Selective MOVPE**  
T. Murase, T. Tanikawa, Y. Honda, M. Yamaguchi and N. Sawaki  
Nagoya University, Japan
- PA049B **Near-Surface Trap Concentration Profiles in n-GaN Determined by Double Correlation Deep-Level Transient Spectroscopy**  
<sup>1</sup>Y. Tokuda, <sup>1</sup>T. Shibata, <sup>1</sup>Y. Yamada, <sup>1</sup>H. Tsuji, <sup>1</sup>T. Onishi, <sup>1</sup>K. Akiyama, <sup>2</sup>H. Ueda, <sup>2</sup>N. Soejima and <sup>2</sup>T. Kachi  
<sup>1</sup>Aichi Institute of Technology, Japan  
<sup>2</sup>Toyota Central R&D Labs. Inc., Japan
- PA050B **Si<sub>3</sub>N<sub>4</sub> Passivation Effects on AlGaIn/GaIn Heterostructures with *n*-GaIn, *i*-GaIn, *p*-GaIn and In<sub>0.04</sub>GaIn Cap Layers**  
S. Arulkumaran and G.I. Ng  
Nanyang Technological University, Singapore
- PA051C **Control of Fluorine Content for Hardness Increase of Amorphous Carbon Film Coated by Pulsed-Plasma Ablation**  
<sup>1</sup>S. Kawara, <sup>2</sup>H. Koizumi, <sup>1</sup>H. Kousaka, <sup>3</sup>K. Yamada and <sup>1</sup>N. Umehara  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Japan Aerospace Exploration Agency, Japan  
<sup>3</sup>ASAHI GLASS Co., Ltd, Japan

- PA052C **Basic Study on Development of Ultra-High-Speed DLC Coating Process**  
T. Okamoto, H. Kousaka and N. Umehara  
Nagoya University, Japan
- PA053C **Tribological Properties of DLC-Coated Inner Surface of Narrow Metal Tube by MVP Method**  
K. Mori, H. Kousaka and N. Umehara  
Nagoya University, Japan
- PA054C **Magneto-Optical Properties of Monolayer and AB-Stacked Bilayer Graphenes**  
<sup>1,2</sup>Y.-H. Ho, <sup>2</sup>Y. H. Chiu, <sup>2</sup>J. Wang, <sup>1</sup>D. H. Lin and <sup>2</sup>M.-F. Lin  
<sup>1</sup>National Sun Yat-Sen University, Taiwan  
<sup>2</sup>National Cheng Kung University, Taiwan
- PA055C **The Effect of Superhydrophobicity on the Wear of a Double Roughening DLC Film**  
Y.-J. Jang, H. Kousaka and N. Umehara  
Nagoya University, Japan
- PA056C **Crystallite Size Control of Multilayer Graphene Thin Films Fabricated by DC Plasma-Enhanced CVD Method**  
<sup>1,2</sup>A. Yoshimura, <sup>1</sup>H. Yoshimura and <sup>1</sup>M. Tachibana  
<sup>1</sup>Yokohama City University, Japan  
<sup>2</sup>IHI Corporation, Japan
- PA057C **Formation of Porous Carbon Film for Electric Double Layer Capacitor by Pulsed DC Plasma CVD Using Ni Catalysis**  
M. Matsushima, M. Noda, G. Kalita, H. Uchida and M. Umeno  
Chubu University, Japan
- PA058C **White Light Photoluminescence from Mesoporous Carbon-Silica Nanocomposite**  
<sup>1</sup>Y. Ishii, <sup>1</sup>A. Matsumura, <sup>1,2</sup>Y. Ishikawa and <sup>1</sup>S. Kawasaki  
<sup>1</sup>Nagoya Institute of Technology, Japan  
<sup>2</sup>Japan Fine Ceramics Center, Japan
- PA059C **Electric Double Layer Capacitance of the Graphene-Like Materials Derived from Single-Walled Carbon Nanotubes**  
T. Inoue, S. Mori and S. Kawasaki  
Nagoya Institute of Technology, Japan
- PA060C **Electronic Property Modification of Single-Walled Carbon Nanotubes by Wrapping ssDNA in Electrolyte Plasma**  
Y. Li, T. Kaneko and R. Hatakeyama  
Tohoku University, Japan



- PA061C **Fabrication of Calcium Atoms Encapsulated Single-Walled Carbon Nanotubes Using Calcium Plasma**  
<sup>1</sup>Y. Osanai, <sup>1</sup>T. Shimizu, <sup>1</sup>T. Kato, <sup>2</sup>W. Oohara and <sup>1</sup>R. Hatakeyama  
<sup>1</sup>Tohoku University, Japan  
<sup>2</sup>Yamaguchi University, Japan
- PA062C **Novel Carbon Composite Modified with Atmospheric Pressure Plasma for Improvement of Electric Double-Layer Capacitance and High Rate Capability**  
H. C-Te and W-Y. Chen  
Yuan Ze University, Taiwan
- PA063C **Ar-Diluted CH<sub>4</sub> Concentration Dependence of the Crystallinity of Multilayer Graphene Grown by Photoemission-Assisted Plasma-Enhanced CVD**  
<sup>1</sup>H. Sumi, <sup>1,2</sup>S. Ogawa, <sup>2,3</sup>M. Sato, <sup>2,3</sup>M. Nihei and <sup>1,2</sup>Y. Takakuwa  
<sup>1</sup>Tohoku University, Japan  
<sup>2</sup>JST, CREST, Japan  
<sup>3</sup>Fujitsu Limited, Japan
- PA064C **Hydrogen Ething Effect of CNW Prepared in Microwave Plasma Enhanced Chemical Vapor Deposition**  
S. Suzuki and M. Yoshimura  
Toyota Technological Institute, Japan
- PA065C **Improvement of Field Electron Emission Performance of Natural Precursor Grown Carbon Nanofibers by Thermal Annealing in an Argon Atmosphere**  
P. Ghosh, T. Soga, T. Jimbo, M. Zamri, S. Hashimoto, H. Ohashi and M. Tanemura  
Nagoya Institute of Technology, Japan
- PA066C **Control in Morphology and Size of Room-Temperature Grown Carbon Nanofibers**  
M. Z. Yusop, K. Yamaguchi, T. Suzuki, P. Ghosh, A. Hayashi, Y. Hayashi and M. Tanemura  
Nagoya Institute of Technology, Japan
- PA067C **Correlation of Mass Density on Tribological Parameters in Diamon-Like Carbon Prepared by Variety of Methods**  
<sup>1</sup>S. Kaneko, <sup>1</sup>T. Horiuchi, <sup>1</sup>K. Yoshida, <sup>1</sup>S. Tanaka, <sup>1</sup>C. Kato, <sup>1</sup>M. Kano, <sup>1</sup>M. Kumagai, <sup>2</sup>H. Tanoue, <sup>2</sup>M. Kamiya and <sup>2</sup>H. Takikawa  
<sup>1</sup>Kanagawa Prefectural Government, Japan  
<sup>2</sup>Toyohashi University of Technology, Japan
- PA068C **DLC Coating on Alumina by MW-PECVD Technique**  
C. Rattanasatien, N. Tonanon and B. Paosawatyanong  
Chulalongkorn University, Thailand

- PA069C **Effect of Sulfur Doped Diamond-Like Carbon Films on the Electrical Properties by DC Magnetron Sputtering**  
A. Saeheng, N. Tonanon and B. Paosawatyanong  
Chulalongkorn University, Thailand
- PA070C **Control of Hydrophilic and Hydrophobic Properties of Carbon Nanowall by Plasma Surface Treatment**  
<sup>1</sup>H. Watanabe, <sup>1</sup>M. Hiramatsu and <sup>2</sup>M. Hori  
<sup>1</sup>Meijo University, Japan  
<sup>2</sup>Nagoya University, Japan
- PA071C **Gas Flow Rate Ratio Dependence of Deposition Profile of H-Assisted Plasma CVD Carbon Films on Trench Substrates**  
<sup>1</sup>T. Nomura, <sup>1</sup>Y. Korenaga, <sup>1</sup>J. Umetsu, <sup>1,4</sup>K. Koga, <sup>1,4</sup>M. Shiratani, <sup>2,4</sup>Y. Setsuhara, <sup>3,4</sup>M. Sekine and <sup>3,4</sup>M. Hori  
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- PA072C **Ultraviolet Ray Irradiation Effect on Frictional Behavior of Carbon Nitride Coating**  
<sup>1</sup>T. Tokoroyama, <sup>1</sup>M. Kamiya, <sup>2</sup>Y. Fuwa and <sup>1</sup>N. Umehara  
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<sup>2</sup>Toyota Motors Co., Ltd., Japan
- PA073C **Ashing Removal of DLC Film by Oxygen-Dominated Plasma Beam Converted from Filtered Carbon-Cathodic Arc Plasma**  
<sup>1</sup>H. Tanoue, <sup>1,2</sup>M. Kamiya, <sup>1</sup>Y. Suda, <sup>1</sup>H. Takikawa, <sup>3</sup>S. Oke, <sup>4</sup>Y. Hasegawa, <sup>4</sup>M. Taki, <sup>4</sup>N. Tsuji, <sup>5</sup>T. Ishikawa and <sup>6</sup>H. Yasui  
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- PA074C **Growth of Graphite Thin Films During DC Plasma-Enhanced Chemical Vapor Deposition**  
<sup>1</sup>H. Yoshimura, <sup>1,2</sup>A. Yoshimura and <sup>1</sup>M. Tachibana  
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- PA075C **Effect of Filament Discharge on Stand-Up of Carbon Nanotwists Tightly-Adhered to Substrate**  
<sup>1</sup>M. Yokota, <sup>1</sup>Y. Sugioka, <sup>1</sup>Y. Suda, <sup>1</sup>H. Takikawa, <sup>2</sup>H. Ue, <sup>3</sup>Y. Umeda and <sup>4</sup>K. Shimizu  
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<sup>3</sup>Toho Gas Co., Ltd., Japan  
<sup>4</sup>Shonan Plastic Mfg. Co., Ltd., Japan
- PA076C **Synthesis of B-Doped Single-Walled Carbon Nanotube Films by Arc Discharge**  
H. Wang, T. Maruyama, S. Inoue and Y. Ando  
Meijo University, Japan
- PA077C **Nitrogen-Modulated Wet-Chemical Decoration of Carbon Nitride/ZnO Hetero-Junction Film Results Enhanced Field-Emission Performance**  
K. Ghosh, M. Kumar, T. Maruyama and Y. Ando  
Meijo University, Japan
- PA078C **Preparation of Arc Black and Carbon Nano-Balloon by Arc Discharge and Their Application to Fuel Cell**  
<sup>1</sup>T. Ikeda, <sup>1</sup>S. Kaida, <sup>1</sup>Y. Suda, <sup>1</sup>H. Takikawa, <sup>2</sup>S. Oke, <sup>3</sup>H. Ue, <sup>4</sup>T. Okawa, <sup>4</sup>N. Aoyagi and <sup>5</sup>K. Shimizu  
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- PA079C **Magneto-Optical Properties of Armchair Nanographene Ribbons Under the Modulated Electric Field**  
S. C. Chen, C. W. Chiu and M. F. Lin  
National Cheng Kung University, Taiwan
- PA080C **Characterization of Nano-polygonal Carbons Synthesized by Arc Discharge Method**  
<sup>1</sup>J-H. Lin, <sup>1</sup>B-H. Li and <sup>2</sup>C-S. Chen  
<sup>1</sup>National University of Tainan, Taiwan  
<sup>2</sup>Chang Gung University, Taiwan
- PA081C **Encapsulation of Fullerenes and Helicity Induction in Syndiotactic PMMA**  
A. Kitaura, H. Iida and E. Yashima  
Nagoya University, Japan

- PA082C **Effects of Oxygen Etching on the Morphologies of Carbon Nanowalls**  
<sup>1</sup>H. Shimoeda, <sup>1</sup>Y. Miyawaki, <sup>1</sup>K. Takeda, <sup>1</sup>K. Ishikawa, <sup>1</sup>H. Kondo, <sup>2</sup>M. Hiramatsu, <sup>1,3</sup>M. Sekine and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Meijo University, Japan  
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- PA083C **Synthesis of SWNTs by Arc Plasma Reactor with Twelve-Phase Alternating Discharge System and Raman Spectroscopic Study**  
<sup>1</sup>B. Chen, <sup>2</sup>T. Matsuura, <sup>1</sup>S. Inoue and <sup>1</sup>Y. Ando  
<sup>1</sup>Meijo University, Japan  
<sup>2</sup>Industrial Technology Center of Fukui Prefecture, Japan
- PA084C **Initial Nucleation in Carbon Nanowalls Growth on Si and SiO<sub>2</sub> Surfaces**  
<sup>1</sup>H. Mikuni, <sup>1</sup>T. Kanda, <sup>1</sup>S. Kondo, <sup>1</sup>W. Takeuchi, <sup>2</sup>K. Yamakawa, <sup>1</sup>K. Takeda, <sup>1</sup>K. Ishikawa, <sup>1</sup>H. Kondo, <sup>3</sup>M. Hiramatsu, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
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- PA085C **Effects of Ion Irradiation on Carbon Nanowalls Growth**  
<sup>1</sup>S. Kondo, <sup>1</sup>K. Yasuda, <sup>1</sup>H. Kondo, <sup>1</sup>K. Ishikawa, <sup>2</sup>M. Hiramatsu, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Meijo University, Japan
- PA086C **Effects of Plasma Surface Treatments on Supporting of Platinum Nanoparticles to Graphite Materials in Supercritical Carbon Dioxide**  
<sup>1</sup>K. Mase, <sup>2</sup>S. Mitsuguchi, <sup>1</sup>S. Kondo, <sup>3</sup>H. Kano, <sup>1</sup>K. Ishikawa, <sup>1</sup>H. Kondo, <sup>2</sup>M. Hiramatsu, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
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<sup>2</sup>Meijo University, Japan  
<sup>3</sup>NU Eco Engineering, Co., Ltd., Japan
- PA087C **Transport of Graphite Cathodic Vacuum Arc Plasma through T-Shape Filter**  
S. Lee, J-K. Kim, J-Y. Lee, S-H. Yun and D-G. Kim  
Korea Institute of Materials Science, Korea
- PA088C **Properties of Tetrahedral Amorphous Carbon Film Prepared by a T-Shape Filter Vacuum Arc Source**  
S. Lee, D-G. Kim, J-Y. Lee, S-H. Yun and J-K. Kim  
Korea Institute of Materials Science, Korea

- PA089C **Effect of Nitrogen Content on Friction Coefficient of Si-Containing Hydrogenated Carbon Nitride Film Deposited by Plasma-Enhanced Chemical Vapor Deposition**  
<sup>1</sup>H. Sakakibara, <sup>1</sup>H. Kousaka, <sup>1</sup>T. Tokoroyama, <sup>1</sup>N. Umehara and <sup>2</sup>Y. Fuwa  
<sup>1</sup>Nagoya University, Japan  
<sup>2</sup>Toyota Motors Co., Ltd., Japan
- PA090C **Optimized Distribution and Morphology of Carbon Nanofibers for a Field Emitter Grown by Plasma-Enhanced CVD Process**  
N. Shimoi and S-I. Tanaka  
Tohoku University, Japan
- PA091C **Low Temperature Growth of ZnO Nanorods on Flexible Polymeric Substrates**  
C-T. Hsieh and C-Y. Lin  
Yuan Ze University, Taiwan
- PA092C **Ruthenium (II) Complexes with Triarylamine and Triarylmethane Derivatives for Efficient Dye-Sensitized Solar Cells**  
<sup>1</sup>Y. Li, <sup>2</sup>Z. Jin, <sup>1</sup>T. Inomata, <sup>1</sup>H. Masuda, <sup>2</sup>N. Yamanaka and <sup>2</sup>M. Minami  
<sup>1</sup>Nagoya Institute of Technology, Japan  
<sup>2</sup>Nippon Oil Corporation, Japan
- PA093C **Fabrication of the CIGS Pellet and Characterization of the Thin Film**  
<sup>1</sup>A. R. Lee, <sup>1</sup>H. S. Jeon, <sup>1</sup>G. S. Lee, <sup>1</sup>D. W. Cho, <sup>1</sup>J. E. Ok, <sup>1</sup>K. H. Kim, <sup>1</sup>M. Yang, <sup>1</sup>H. S. Ahn, <sup>2</sup>C. R. Cho and <sup>3</sup>H. Ha  
<sup>1</sup>Korea Maritime University, Korea  
<sup>2</sup>Pusan National University, Korea  
<sup>3</sup>CS Solution Co., Ltd., Korea
- PA094C **Optimization of ZnO/Eosin Y Hybrid Film Based Solar Cells Using Ruthenium Complex as Dye Sensitizers**  
<sup>1</sup>X-F. Wang, <sup>1</sup>T. Yoshida, <sup>2</sup>T. Inomata and <sup>2</sup>H. Masuda  
<sup>1</sup>Gifu University, Japan  
<sup>2</sup>Nagoya Institute of Technology, Japan
- PA095C **Control of Nanostructure and Crystallographic Orientation in Electrodeposition of ZnO Hybrid Thin Films Using Templates**  
<sup>1</sup>K. Ichinose, <sup>1</sup>T. Mizuno, <sup>2</sup>S. Morishta, <sup>2</sup>J. Yamasaki, <sup>2</sup>N. Tanaka and <sup>1</sup>T. Yoshida  
<sup>1</sup>Gifu University, Japan  
<sup>2</sup>Nagoya University, Japan
- PA096C **A New Hetrojunction Solar Cell Base on (n) Pentance/(i) a-Si:H/(p) a-Si:H**  
C-H. Chao, C-H. Chan and P-Y. Chen  
Mingdao University, Taiwan

- PA097C **Fabrication of F-Doped Tin Oxide Film for Dye Sensitized Solar Cells**  
M. Oshima and K. Yoshino  
University of Miyazaki, Japan
- PA098C **Preparation and Characterization of Nanocrystalline ITO Thin Films on Glass and Clay Substrates by Ion-Beam Sputter Method**  
S. Venkatachalam, H. Nanjo, F. M. B. Hassan, N. Teshima, K. Kawasaki, M. Kanakubo, T. Aizawa, T. Aida and T. Ebina  
National Institute of Advanced Industrial Science & Technology (AIST), Japan
- PA099C **Activation of Dioxygen by Copper Complexes with *N*-Alkylated *cis,cis*-1,3,5-Triaminocyclohexane Ligands**  
J. Matsumoto, Y. Kajita, Y. Funahashi, T. Ozawa and H. Masuda  
Nagoya Institute of Technology, Japan
- PA100C **Development of Sulfur Containing Copper(II) Complex Activating O-O Bond**  
<sup>1</sup>Y. Kajita, <sup>1</sup>T. Tozuka, <sup>1</sup>Y. W-Tsutsui, <sup>2</sup>M. Kubo, <sup>2</sup>T. Ogura and <sup>1</sup>H. Masuda  
<sup>1</sup>Nagoya Institute of Technology, Japan  
<sup>2</sup>University of Hyogo, Japan
- PA101C **Development of Copper Complex Catalysts that Hydroxylate Benzene**  
M. Goto, Y. Kajita, Y. Funahashi, T. Ozawa and H. Masuda  
Nagoya Institute of Technology, Japan
- PA102C **Dinitrogen Activation Using Mononuclear Mo Complexes with P-N-P Bond**  
T. Ogawa, Y. Kajita and H. Masuda  
Nagoya Institute of Technology, Japan
- PA103C **Photoluminescence of Tetragonal and Monoclinic ZrO<sub>2</sub>:Eu Nanocrystals Synthesized by Sol-Gel Route**  
L. Li, H. K. Yang, B. K. Moon, B. C. Choi and J. H. Jeong  
Pukyong National University, Korea
- PA104C **Luminescence Properties of LiYO<sub>2</sub>:Eu<sup>3+</sup> Nanophosphors by Solvothermal Method**  
<sup>1</sup>J. W. Chung, <sup>1</sup>B. K. Moon, <sup>1</sup>B. C. Choi, <sup>1</sup>J. H. Jeong, <sup>2</sup>K. Jang, H. S. Lee and <sup>3</sup>S. S. Yi  
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<sup>3</sup>Silla University, Korea

- PA105C **Synthesis and Photoluminescence Properties BaY<sub>2</sub>ZnO<sub>5</sub>:Eu<sup>2+</sup> Thin Film White Phosphors by PLD**  
<sup>1</sup>H. K. Yang, <sup>1</sup>B. K. Moon, <sup>1</sup>B. C. Choi, <sup>1</sup>J. H. Jeong and <sup>2</sup>J. H. Kim  
<sup>1</sup>Pukyong National University, Korea  
<sup>2</sup>Donguei University, Korea
- PA106C **Shape Transitions of Ag Precipitates During Aging in Cu-Ag Single Crystals**  
T. Miyazawa, T. Fujii, S. Onaka and M. Kato  
Tokyo Institute of Technology, Japan
- PA107C **Magnetic Properties of FePd Nanoparticles Synthesized by Microwave Applied Heatings**  
<sup>1</sup>K. Honda, <sup>1</sup>T. Wakabayashi, <sup>1</sup>T. Matsuse, <sup>1</sup>M. Kimura and <sup>2</sup>M. Taya  
<sup>1</sup>Shinshu University, Japan  
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- PA108C **Microwave-assisted Deposition of Pt Catalysts on Carbon Nanotube/Carbon Paper Electrodes**  
C-T. Hsieh, W-M. Hung, J-M. Wei and S-M. Hsu  
Yuan Ze University, Taiwan
- PA109C **Structural Change of InGaN Nano-Structures Grown by Mixed Source HVPE**  
<sup>1</sup>H. S. Jeon, <sup>1</sup>H. S. Ahn, <sup>1</sup>A. R. Lee, <sup>1</sup>K. S. Lee, <sup>1</sup>D. W. Cho, <sup>1</sup>J. E. Ok, <sup>1</sup>K. H. Kim, <sup>1</sup>S. N. Yi, <sup>1</sup>M. Yang, <sup>2</sup>C. K. Kim and <sup>3</sup>H. Ha  
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- PA110C **Synthesis and Luminescence Properties of Ce<sup>3+</sup> Doped Aluminum Garnet Crystalline Powders**  
<sup>1</sup>H. C. Jung, <sup>1</sup>J. Y. Park, <sup>1</sup>G. S. R. Raju, <sup>1</sup>J. H. Jeong, <sup>1</sup>B. K. Moon, <sup>2</sup>J. H. Kim and <sup>2</sup>H. Y. Cho  
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<sup>2</sup>Donguei University, Korea
- PA111C **Three-Dimensionally Ordered Macroporous ZrO<sub>2</sub>: Tb<sup>3+</sup> Films: Synthesis, Characterization and Photoluminescence Properties**  
X. Qu, H. K. Yang and J. H. Jeong  
Pukyong National University, Korea
- PA112C **Thermal Fluid-Flow Behaviour of Aqueous Suspensions of Nanoparticles Flowing in Constant Heat Flux Heating Circular Pipe**  
S. Torii  
Kumamoto University, Japan

- PA113C **Growth of AgInSe<sub>2</sub> Nano Crystal Grown by Non-Vacuum Process**  
A. Nagaoka and K. Yoshino  
University of Miyazaki, Japan
- PA114C **Magnetic Properties of Fe-Co Cluster and Fe-Pt Thin Film Composites Prepared by Plasma-Gas-Condensation and Helicon-Wave-Assisted Magnetron Sputtering**  
<sup>1</sup>K. Sumiyama, <sup>1</sup>S. Sawa, <sup>1</sup>Y. Kurokawa, <sup>2</sup>D. L. Peng and <sup>1</sup>T. Hihara  
<sup>1</sup>Nagoya Institute of Technology, Japan  
<sup>2</sup>Xiamen University, China
- PA115C **Ni-Based Alloy Clusters Produced by Plasma-Gas-Condensation for Catalysts in Electrode of Polymer Electrolyte Fuel Cell**  
T. Hihara, S. Inoue, T. Morita and K. Sumiyama  
Nagoya Institute of Technology, Japan
- PA116C **Low-Temperature Treatment Using High-Density Non-Equilibrium Atmospheric Pressure Plasma**  
<sup>1</sup>S. Iseki, <sup>2</sup>S. Uchida, <sup>2</sup>S. Takashima, <sup>3</sup>T. Ohta, <sup>4</sup>M. Ito, <sup>5</sup>Y. Higashijima, <sup>6</sup>H. Kano, <sup>1</sup>K. Takeda, <sup>1</sup>H. Kondo, <sup>1</sup>K. Ishikawa, <sup>1</sup>M. Sekine and <sup>1</sup>M. Hori  
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<sup>4</sup>Meijo University, Japan  
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<sup>6</sup>NU Eco Engineering Co., Ltd., Japan
- PA117A **Aligning and Immobilizing DNA-Templated Gold Nanoparticle Chains on Si Chip for the Application to Nanodevices**  
<sup>1</sup>H. J. Kim, <sup>2</sup>S. Cha, <sup>1</sup>Y. Roh and <sup>1</sup>B. Hong  
<sup>1</sup>Sungkyunkwan University, Korea  
<sup>2</sup>System Technology Excellence (STX) Engine, Korea
- PA118A **Structural, Electrical and Optical Properties of SnO<sub>2</sub>:Sb Films Prepared on Flexible Substrate at Room Temperature**  
S. U. Lee, J-H. Boo and B. Hong  
Sungkyunkwan University, Korea
- PA119A **Low Temperature GaN Epitaxial Growing Assisted by Hyperthermal Neutral Beams**  
<sup>1</sup>S. J. Yoo, <sup>1,2</sup>S. B. Kim, <sup>1</sup>D. C. Kim, <sup>1</sup>I-K. Yu and <sup>2</sup>M. Cho  
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